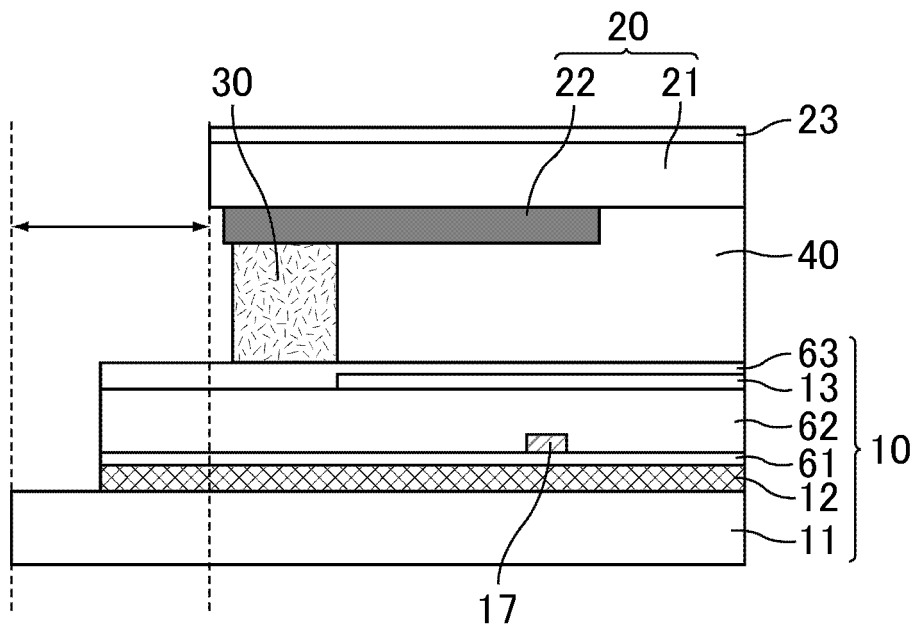


[図1]



[図2]

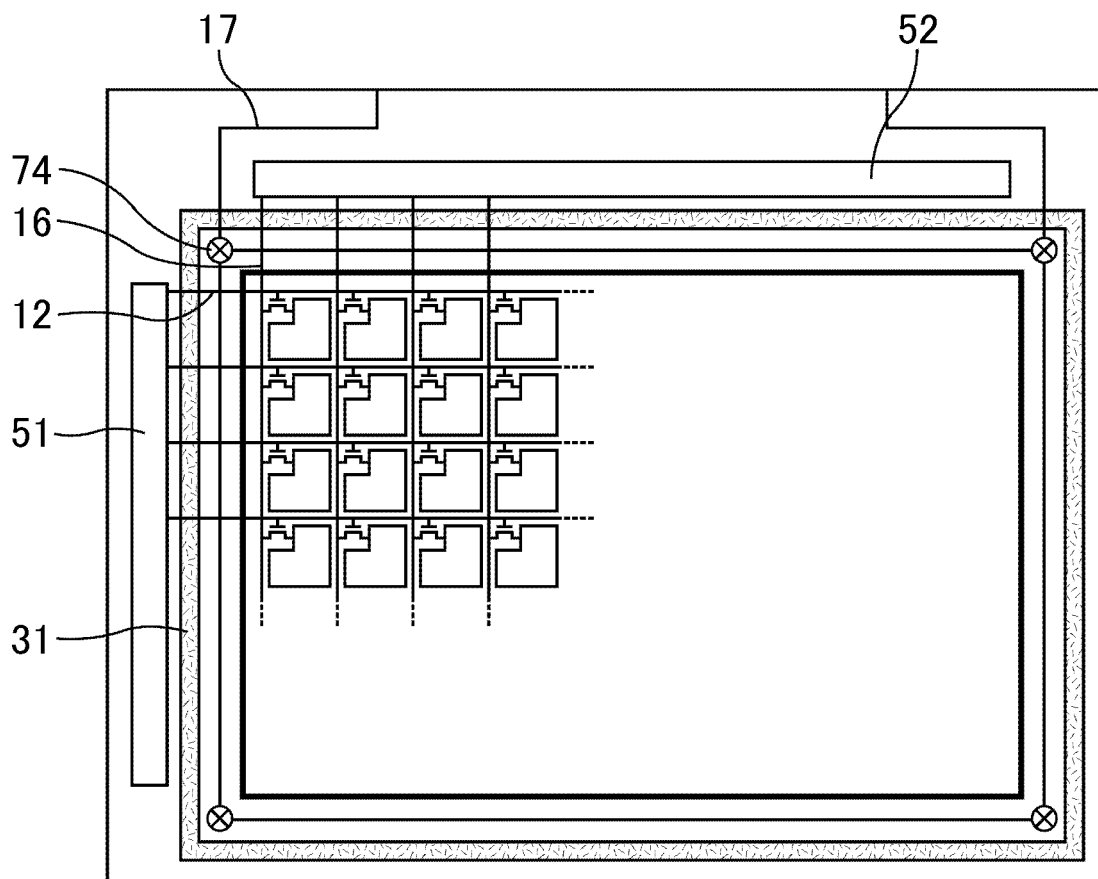
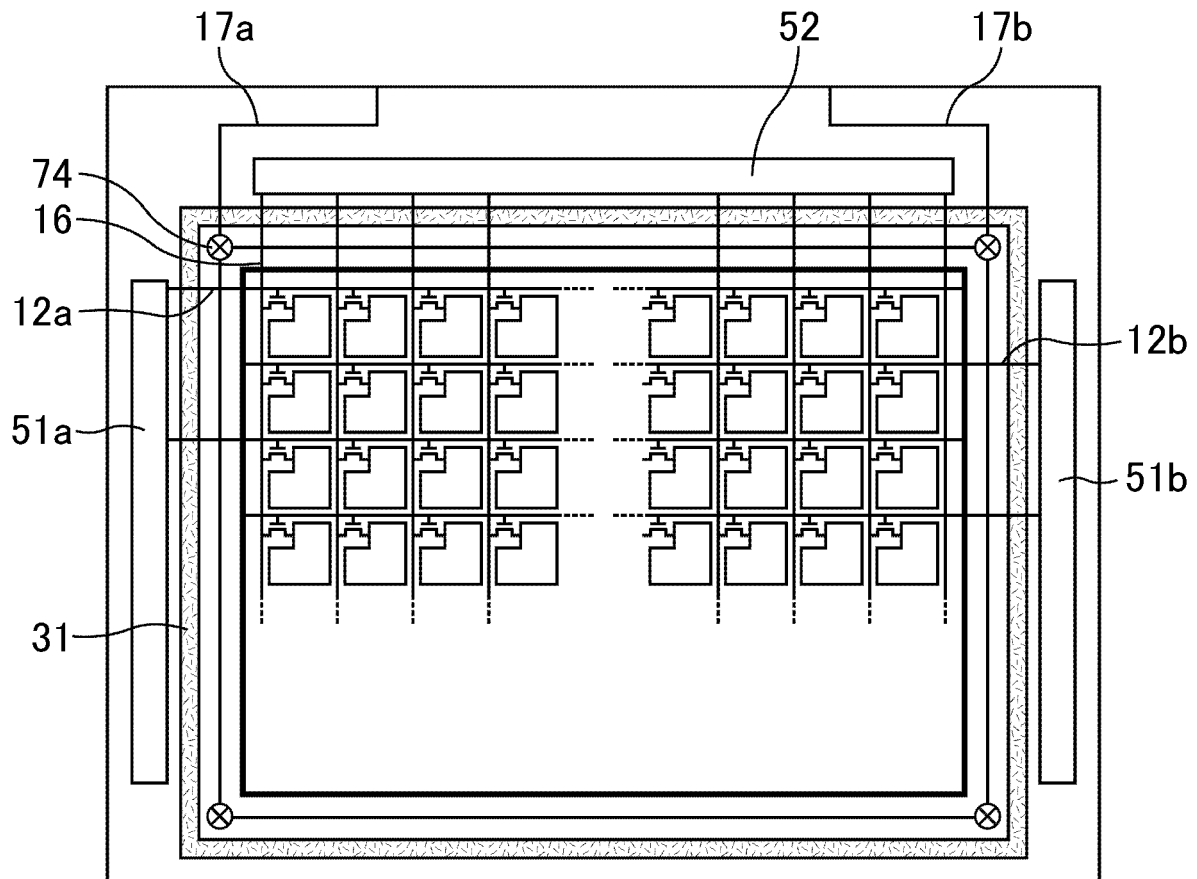


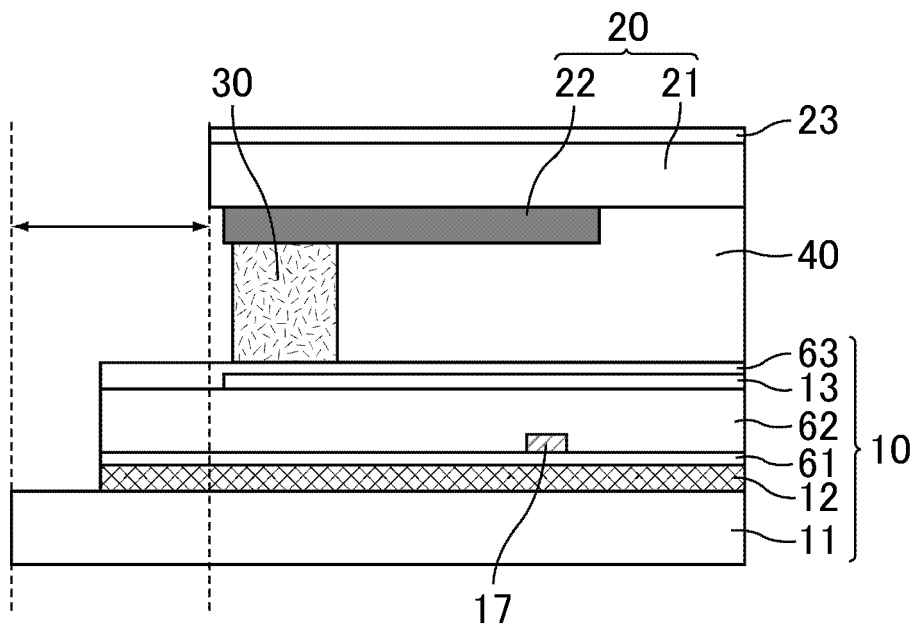
Diagram illustrating a rectangular frame structure. The frame is defined by a vertical line on the left and a horizontal line on the top. Seven rectangular blocks are arranged within the frame:

- Block 13 is located at the top-left corner.
- Block 56a is located in the middle-left area.
- Block 56b is located at the bottom-left corner.
- Three blocks are arranged in a horizontal row in the middle-right area.
- Three blocks are arranged in a horizontal row at the bottom-right area.

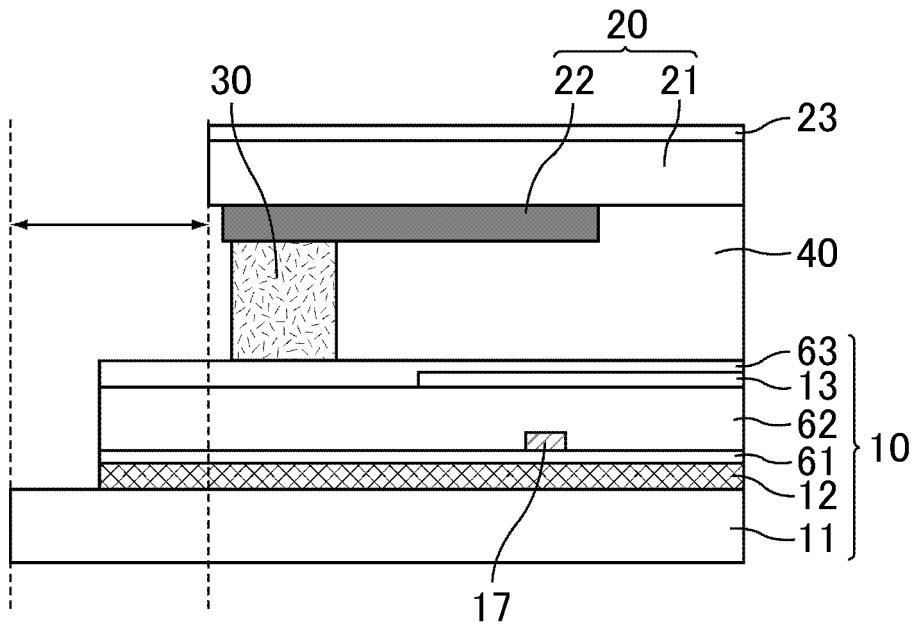
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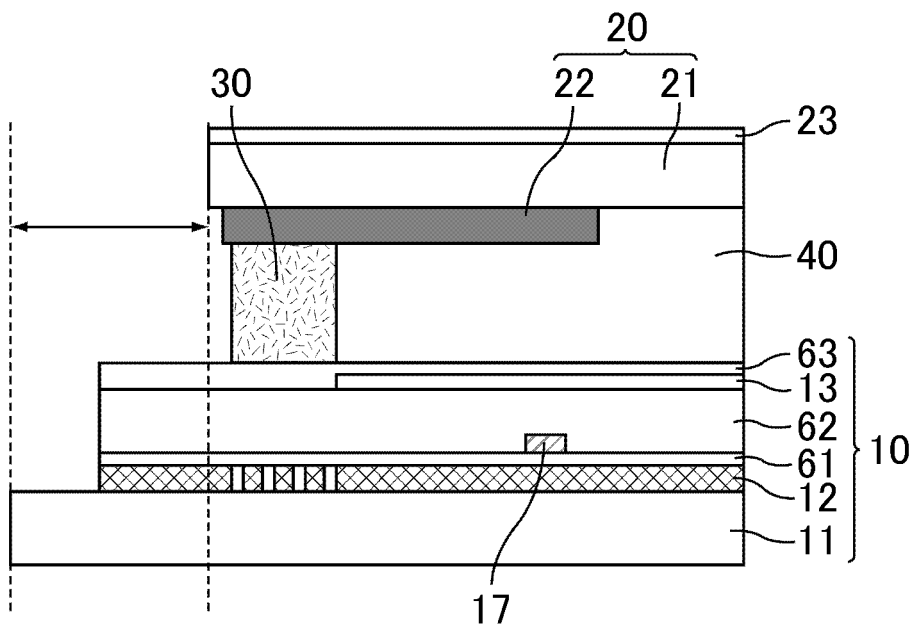
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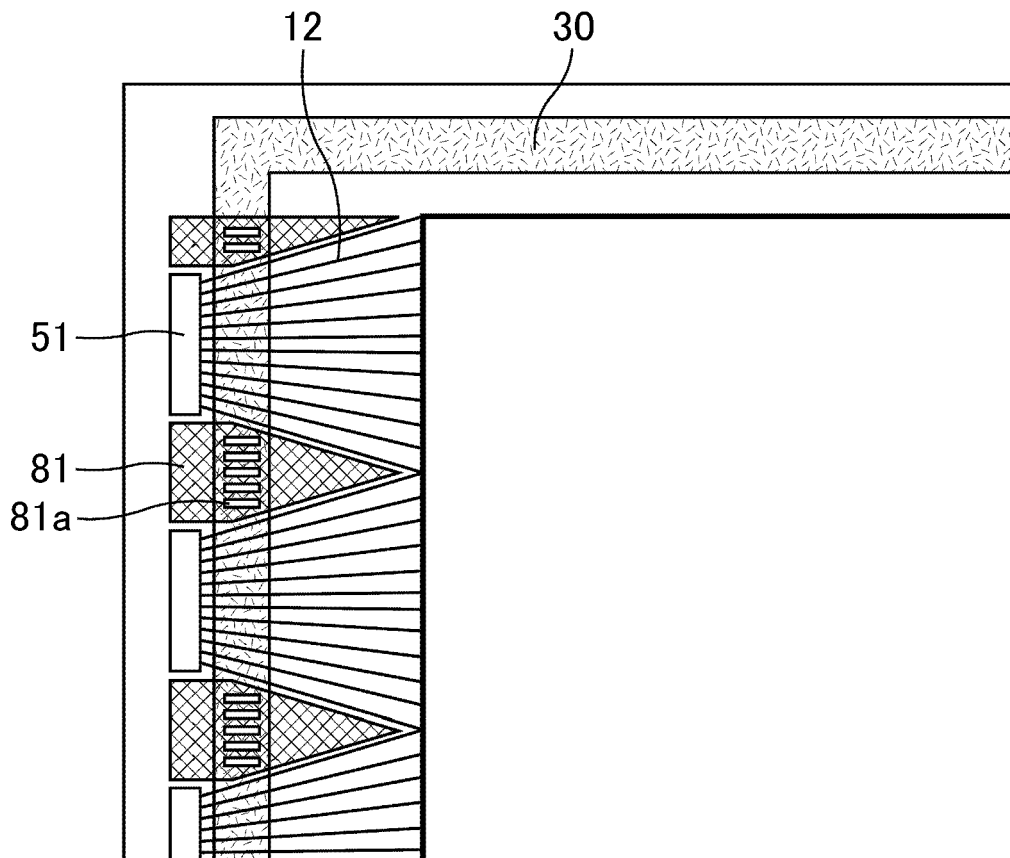
[図7]



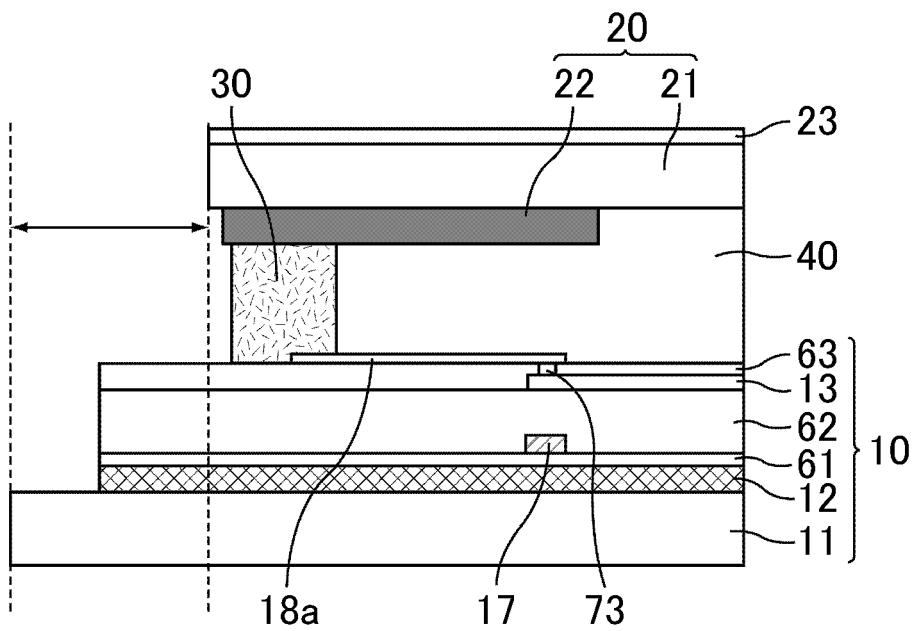
[図8]



[図9]



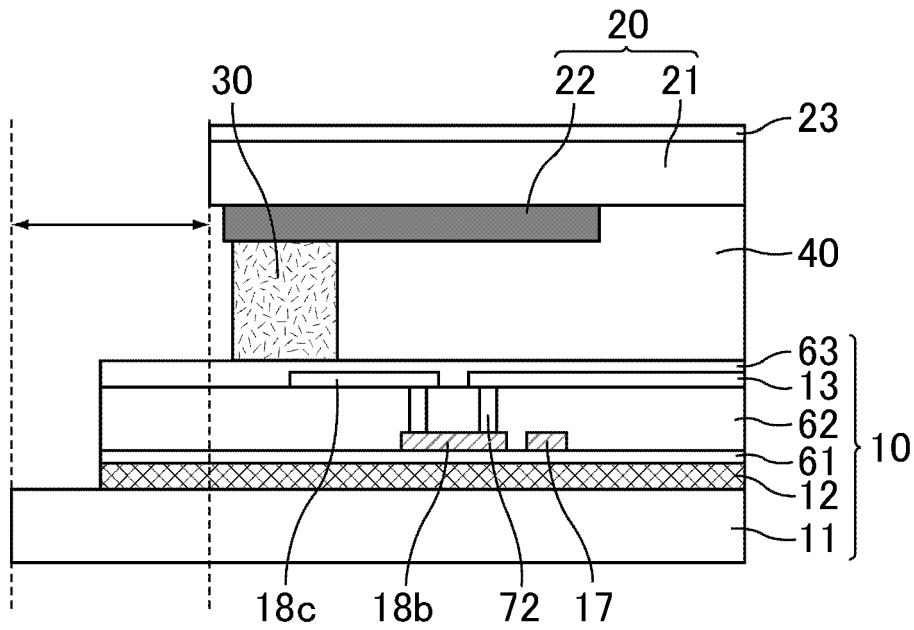
[図10]



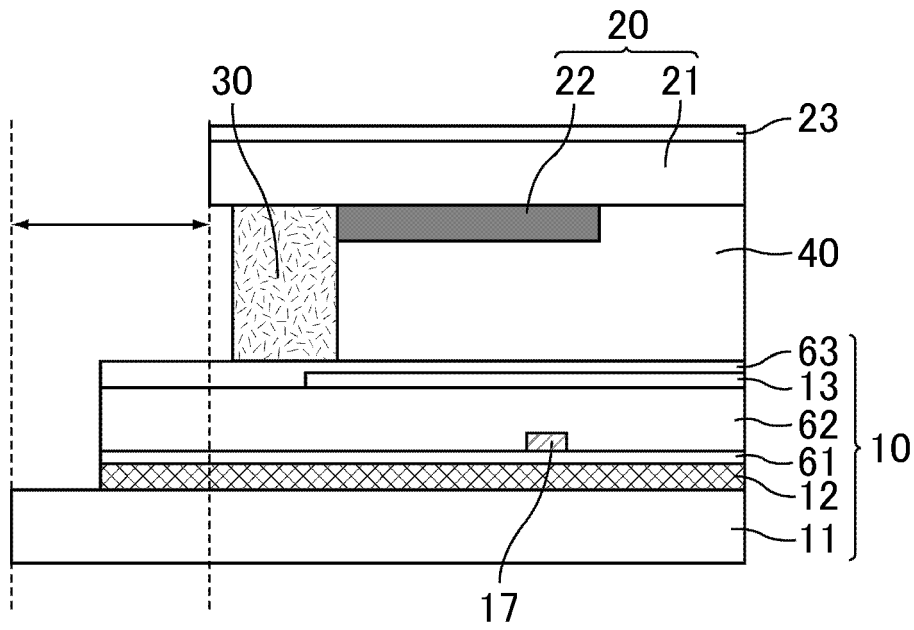
A cross-sectional view of a semiconductor device 10. The device consists of a substrate 11 with a cross-hatched pattern. Above the substrate is a layer 12 with a diagonal line pattern. On top of layer 12 are three rectangular regions: 17 (hatched), 72 (white), and 18b (hatched). Above these is a layer 61 with a diagonal line pattern. Above layer 61 is a layer 62 with a diagonal line pattern. Above layer 62 is a layer 13 with a diagonal line pattern. Above layer 13 is a layer 63 with a diagonal line pattern. A vertical structure 40 is located on the left side of the device. It consists of a base 30 with a stippled pattern, a layer 22 with a diagonal line pattern, and a top layer 21 with a diagonal line pattern. A bracket 20 groups layers 21 and 22. A layer 23 is on the right side of the device. A dashed vertical line is on the left side of the device. An arrow points from the left towards the device.

[illegible]

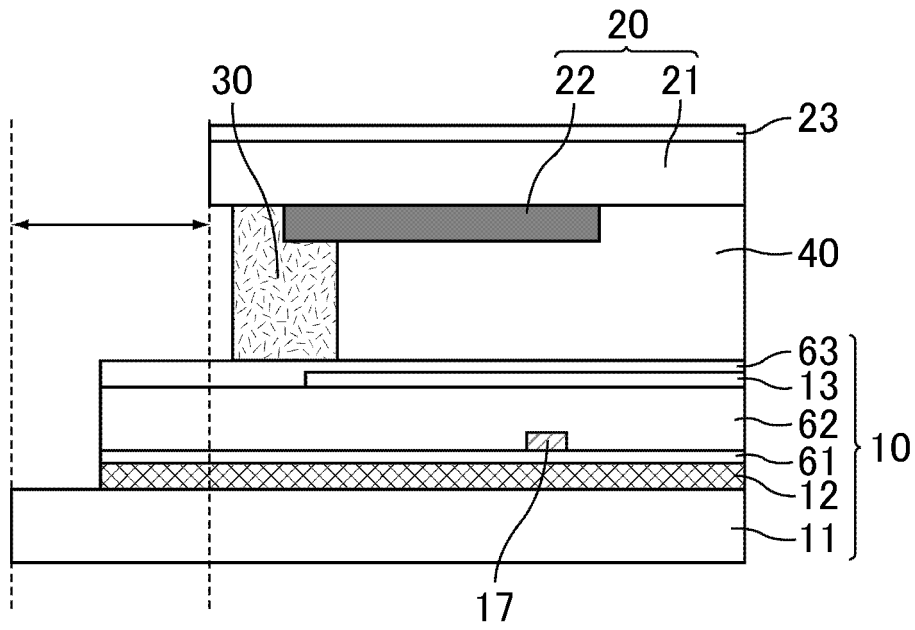
[図13]



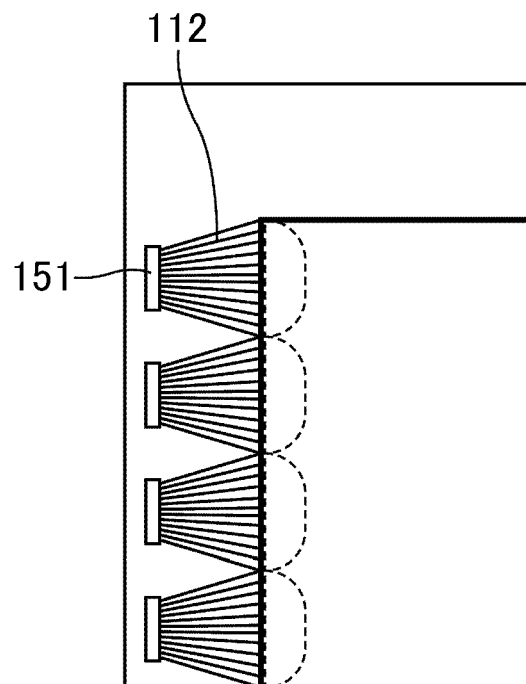
[図14]



[図15]



[図16]



[図17]

